

Nuno P S L N F Franco

List of Publications by Year in descending order

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109
papers

2,285
citations

304743

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docs citations

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times ranked

2938
citing authors

#	ARTICLE	IF	CITATIONS
1	Validity of Vegard's rule for Al _{1-x} In _x N (0.08 ≤ x ≤ 0.28) thin films grown on GaN templates. Physics D: Applied Physics, 2017, 50, 205107.	2.8	10
2	Study of In distribution on GaInSb:Al crystals by ion beam techniques. Nuclear Instruments & Methods in Physics Research B, 2016, 371, 278-282.	1.4	6
3	Structural characterization of dual ion implantation in silicon. Nuclear Instruments & Methods in Physics Research B, 2015, 365, 39-43.	1.4	4
4	Composition, structure and morphology of Al _{1-x} In _x N thin films grown on Al _{1-y} Ga _y N templates with different GaN contents. Journal Physics D: Applied Physics, 2015, 48, 015103.	2.8	7
5	Retention behaviour of deuterium and helium in beryllium under single D ⁺ and dual He ⁺ /D ⁺ exposure. Fusion Engineering and Design, 2015, 98-99, 1362-1366.	1.9	4
6	Formation of oriented nitrides by N ⁺ ion implantation in iron single crystals. Journal of Magnetism and Magnetic Materials, 2014, 350, 129-134.	2.3	4
7	Magnetic and electrical characterization of TiO ₂ single crystals co-implanted with iron and cobalt. Journal of Magnetism and Magnetic Materials, 2014, 364, 106-116.	2.3	9
8	Influence of RF-sputtering power on formation of vertically stacked Si _{1-x} Ge _x nanocrystals between ultra-thin amorphous Al ₂ O ₃ layers: structural and photoluminescence properties. Journal Physics D: Applied Physics, 2013, 46, 385301.	2.8	1
9	Microstructure and nanomechanical properties of Fe ⁺ implanted silicon. Applied Surface Science, 2013, 284, 533-539.	6.1	7
10	CdTe nano-structures for photovoltaic devices. Nuclear Instruments & Methods in Physics Research B, 2013, 306, 218-221.	1.4	2
11	Enhanced red emission from praseodymium-doped GaN nanowires by defect engineering. Acta Materialia, 2013, 61, 3278-3284.	7.9	22
12	Formation of oriented nickel aggregates in rutile single crystals by Ni implantation. Journal of Magnetism and Magnetic Materials, 2013, 340, 102-108.	2.3	7
13	Effects of helium and deuterium irradiation on SPS sintered W-Ta composites at different temperatures. Journal of Nuclear Materials, 2013, 442, S251-S255.	2.7	17
14	Synergistic helium and deuterium blistering in tungsten-tantalum composites. Journal of Nuclear Materials, 2013, 442, 69-74.	2.7	21
15	Formation and delamination of beryllium carbide films. Journal of Nuclear Materials, 2013, 442, S320-S324.	2.7	11
16	Enhanced dynamic annealing and optical activation of Eu implanted a-plane GaN. Europhysics Letters, 2012, 97, 68004.	2.0	15
17	Structural and magnetic properties of thin films of BaFeO _{3-δ} deposited by pulsed injection metal-organic chemical vapor deposition. Journal of Applied Physics, 2012, 111, .	2.5	9
18	Carbon Deposition on Beryllium Substrates and Subsequent Delamination. Materials Science Forum, 2012, 730-732, 179-184.	0.3	0

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19	Single phase a-plane MgZnO epilayers for UV optoelectronics: substitutional behaviour of Mg at large contents. <i>CrystEngComm</i> , 2012, 14, 1637-1640.	2.6	29
20	High temperature phase transitions and critical exponents of Samarium orthoferrite determined by <i>in situ</i> optical ellipsometry. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	15
21	Cd ion implantation in AlN. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012, 289, 43-46.	1.4	6
22	The electronic transport mechanism in indium molybdenum oxide thin films RF sputtered at room temperature. <i>Europhysics Letters</i> , 2012, 97, 36002.	2.0	9
23	Structural and optical studies of Au doped titanium oxide films. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012, 272, 61-65.	1.4	16
24	Characterization of nanostructured HfO ₂ films using RBS and PAC. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012, 273, 195-198.	1.4	1
25	Radiation damage formation and annealing in GaN and ZnO. <i>Proceedings of SPIE</i> , 2011, , .	0.8	54
26	Comparative study of fusion relevant properties of Be ¹² V and Be ¹² Ti. <i>Fusion Engineering and Design</i> , 2011, 86, 2454-2457.	1.9	9
27	Microstructural characterization of the ODS Eurofer 97 EU-batch. <i>Fusion Engineering and Design</i> , 2011, 86, 2386-2389.	1.9	12
28	Golden glazes analysis by PIGE and PIXE techniques. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2011, 269, 3060-3062.	1.4	2
29	Colossal dielectric constant of poly- and single-crystalline CaCu ₃ Ti ₄ O ₁₂ fibres grown by the laser floating zone technique. <i>Acta Materialia</i> , 2011, 59, 102-111.	7.9	27
30	Influence of Deposition Pressure on N-doped ZnO Films by RF Magnetron Sputtering. <i>Journal of Nanoscience and Nanotechnology</i> , 2010, 10, 2674-2678.	0.9	3
31	Cascade of Peritectic Reactions in the B-Fe-U System. <i>Journal of Phase Equilibria and Diffusion</i> , 2010, 31, 104-112.	1.4	4
32	Effect of Eu ₂ O ₃ doping on Ta ₂ O ₅ crystal growth by the laser-heated pedestal technique. <i>Journal of Crystal Growth</i> , 2010, 313, 62-67.	1.5	7
33	Single and polycrystalline mullite fibres grown by laser floating zone technique. <i>Journal of the European Ceramic Society</i> , 2010, 30, 3311-3318.	5.7	20
34	Damage recovery and optical activity in europium implanted wide gap oxides. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2010, 268, 3137-3141.	1.4	5
35	Characterization of mesoporous ZnO:SiO ₂ films obtained by the sol-gel method. <i>Thin Solid Films</i> , 2010, 518, 7002-7006.	1.8	9
36	Al _{1-x} In _x N/GaN bilayers: Structure, morphology, and optical properties. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1740-1746.	1.5	10

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37	Effect of annealing on AlN/GaN quantum dot heterostructures: advanced ion beam characterization and X-ray study of low-dimensional structures. <i>Surface and Interface Analysis</i> , 2010, 42, 1552-1555.	1.8	6
38	High Mobility a-IGO Films Produced at Room Temperature and Their Application in TFTs. <i>Electrochemical and Solid-State Letters</i> , 2010, 13, H20.	2.2	52
39	Hydrogen in InN: A ubiquitous phenomenon in molecular beam epitaxy grown material. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	36
40	Structural anisotropy of nonpolar and semipolar InN epitaxial layers. <i>Journal of Applied Physics</i> , 2010, 108, .	2.5	21
41	Optical and Structural Properties of an Eu Implanted Gallium Nitride Quantum Dots/Aluminium Nitride Superlattice. <i>Journal of Nanoscience and Nanotechnology</i> , 2010, 10, 2473-2478.	0.9	3
42	Depth-resolved analysis of spontaneous phase separation in the growth of lattice-matched AlInN. <i>Journal Physics D: Applied Physics</i> , 2010, 43, 055406.	2.8	33
43	Structural and thermal characterization of SiO ₂ -P ₂ O ₅ sol-gel powders upon annealing at high temperatures. <i>Journal of Non-Crystalline Solids</i> , 2010, 356, 495-501.	3.1	21
44	Influence of oxygen partial pressure on properties of N-doped ZnO films deposited by magnetron sputtering. <i>Transactions of Nonferrous Metals Society of China</i> , 2010, 20, 2326-2330.	4.2	1
45	Structural and optical properties of Zn _{0.9} Mn _{0.1} O/ZnO core-shell nanowires designed by pulsed laser deposition. <i>Journal of Applied Physics</i> , 2009, 106, .	2.5	13
46	Investigation of different mechanisms of GaN growth induced on AlN and GaN nucleation layers. <i>Journal of Applied Physics</i> , 2009, 105, .	2.5	15
47	Room-Temperature Cosputtered HfO ₂ /Al ₂ O ₃ Multicomponent Gate Dielectrics. <i>Electrochemical and Solid-State Letters</i> , 2009, 12, G65.	2.2	22
48	Breakdown of anomalous channeling with ion energy for accurate strain determination in GaN-based heterostructures. <i>Applied Physics Letters</i> , 2009, 95, 051921.	3.3	5
49	Influence of steering effects on strain detection in AlGaInN/GaN heterostructures by ion channelling. <i>Journal Physics D: Applied Physics</i> , 2009, 42, 065420.	2.8	6
50	Ferromagnetism induced in rutile single crystals by argon and nitrogen implantation. <i>Journal of Physics Condensed Matter</i> , 2009, 21, 206002.	1.8	32
51	Europium doping of zincblende GaN by ion implantation. <i>Journal of Applied Physics</i> , 2009, 105, 113507.	2.5	8
52	Characterisation of titanium beryllides with different microstructure. <i>Fusion Engineering and Design</i> , 2009, 84, 1136-1139.	1.9	12
53	Electrical, structural and optical characterization of copper oxide thin films as a function of post annealing temperature. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 2143-2148.	1.8	67
54	Structural and optical properties of nitrogen doped ZnO films. <i>Vacuum</i> , 2009, 83, 1274-1278.	3.5	11

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55	Influence of the AlN molar fraction on the structural and optical properties of praseodymium-doped $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 1$) alloys. <i>Microelectronics Journal</i> , 2009, 40, 377-380.	2.0	15
56	Structural and optical properties on thulium-doped LHPG-grown Ta_2O_5 fibres. <i>Microelectronics Journal</i> , 2009, 40, 309-312.	2.0	10
57	Microstructural evolution in tungsten and copper probes under hydrogen irradiation at ISTTOK. <i>Journal of Nuclear Materials</i> , 2009, 390-391, 1039-1042.	2.7	7
58	Structure of NiCrAlY coatings deposited on single-crystal alloy turbine blade material by laser cladding. <i>Acta Materialia</i> , 2009, 57, 5292-5302.	7.9	118
59	New Approaches to Thermoelectric Materials. NATO Science for Peace and Security Series B: Physics and Biophysics, 2009, , 51-67.	0.3	5
60	Ion Beam Analysis of Iridium-Based TES for Microcalorimeter Detectors. , 2009, , .		0
61	Defect studies on fast and thermal neutron irradiated GaN. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2008, 266, 2780-2783.	1.4	20
62	Anisotropy effects on the formation of new phases in Al_2O_3 by high fluence Zn implantation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2008, 266, 3129-3132.	1.4	1
63	Relaxation of compressively strained AlInN on GaN. <i>Journal of Crystal Growth</i> , 2008, 310, 4058-4064.	1.5	50
64	Effect of post-annealing on the properties of copper oxide thin films obtained from the oxidation of evaporated metallic copper. <i>Applied Surface Science</i> , 2008, 254, 3949-3954.	6.1	226
65	Microwave dielectric permittivity and photoluminescence of Eu_2O_3 doped laser heated pedestal growth Ta_2O_5 fibers. <i>Applied Physics Letters</i> , 2008, 92, 252904.	3.3	6
66	Tuning of oxidation states in the LaNiO_3 perovskite around the insulator-metal transition. <i>Journal of Applied Physics</i> , 2008, 104, 103539.	2.5	11
67	Reversible phase transformation of LaNiO_3 thin films studied in situ by spectroscopic ellipsometry. <i>Physical Review B</i> , 2007, 76, .	3.2	32
68	Structural and Oxidation Studies of Titanium Beryllides. <i>Nuclear Technology</i> , 2007, 159, 233-237.	1.2	2
69	Optical and structural behaviour of Cu-implanted sapphire. <i>Surface and Coatings Technology</i> , 2007, 201, 8190-8196.	4.8	9
70	Synthesis of ZnO nanocrystals in sapphire by ion implantation and vacuum annealing. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007, 257, 515-518.	1.4	14
71	Anisotropic ferromagnetism induced in rutile single crystals by Co implantation. <i>European Physical Journal B</i> , 2007, 55, 253-260.	1.5	15
72	Anomalous Ion Channeling in AlInN/GaN Bilayers: Determination of the Strain State. <i>Physical Review Letters</i> , 2006, 97, 085501.	7.8	125

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73	Growth by LPCVD, crystallization and characterization of SiGe nanoparticles for nanoelectronic devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 1284-1290.	1.8	14
74	RBS and XRD analysis of SiGe/Ge heterostructures for p-HMOS applications. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006, 249, 878-881.	1.4	0
75	Defect production in neutron irradiated GaN. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006, 249, 358-361.	1.4	27
76	Optical and structural behaviour of Mn implanted sapphire. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006, 250, 90-94.	1.4	1
77	Damage behaviour of GaAs/AlAs multilayer structures. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006, 249, 890-893.	1.4	1
78	Irradiation-assisted photoelastic domain wall formation in X- and Y-cut lithium niobate. <i>Solid State Communications</i> , 2006, 137, 296-300.	1.9	0
79	XRD analysis of strained Ge ^δ /SiGe heterostructures on relaxed SiGe graded buffers grown by hybrid epitaxy on Si(001) substrates. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 123-126.	3.5	4
80	Rutherford backscattering and X-ray reflectivity analysis of tunnel barriers. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 240, 365-370.	1.4	1
81	Analysis of nanolayered samples with a 4He beam. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 241, 361-364.	1.4	0
82	Low-temperature molecular beam epitaxy of Ge on Si. <i>Materials Science in Semiconductor Processing</i> , 2005, 8, 35-39.	4.0	3
83	Compositional and structural characterisation of GaSb and GaInSb. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 240, 360-364.	1.4	3
84	Beyond single scattering off flat samples. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 241, 316-320.	1.4	4
85	Ion beam analysis of GaInAsSb films grown by MOVPE on GaSb. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 241, 326-330.	1.4	6
86	High resolution backscattering studies of nanostructured magnetic and semiconducting materials. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 241, 454-458.	1.4	13
87	Characterization and stability studies of titanium beryllides. <i>Fusion Engineering and Design</i> , 2005, 75-79, 759-763.	1.9	2
88	Exchange bias in ordered antiferromagnets by rapid thermal anneal without magnetic field. <i>Journal Physics D: Applied Physics</i> , 2005, 38, 2151-2155.	2.8	16
89	Characterization of CoFeB electrodes for tunnel junctions. <i>Journal of Applied Physics</i> , 2005, 97, 10C916.	2.5	32
90	Direct evidence for strain inhomogeneity in In _x Ga _{1-x} N epilayers by Raman spectroscopy. <i>Applied Physics Letters</i> , 2004, 85, 2235-2237.	3.3	21

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91	Residual stresses and elastic modulus of thermal barrier coatings graded in porosity. Surface and Coatings Technology, 2004, 188-189, 120-128.	4.8	83
92	Degradation of Structural and Optical Properties of InGaN/GaN Multiple Quantum Wells with Increasing Number of Wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 302-306.	0.8	4
93	Analysis of Strain Depth Variations in an In _{0.19} Ga _{0.81} N Layer by Raman Spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 563-567.	0.8	7
94	Structural and optical properties of InGaN/GaN layers close to the critical layer thickness. Applied Physics Letters, 2002, 81, 1207-1209.	3.3	94
95	Strain and composition distributions in wurtzite InGaN/GaN layers extracted from x-ray reciprocal space mapping. Applied Physics Letters, 2002, 80, 3913-3915.	3.3	209
96	Strain relaxation and compositional analysis of InGaN/GaN layers by Rutherford backscattering. Nuclear Instruments & Methods in Physics Research B, 2002, 190, 560-564.	1.4	10
97	Application of high-resolution X-ray diffraction to study strain status in Si _{1-x} Ge _x /Si (001) heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 453-456.	3.5	6
98	Splitting of X-ray diffraction and photoluminescence peaks in InGaN/GaN layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 163-167.	3.5	20
99	Characterisation of corrosion products in Cr implanted Mg surfaces. Surface and Coatings Technology, 2002, 158-159, 328-333.	4.8	27
100	Interpretation of double x-ray diffraction peaks from InGaN layers. Applied Physics Letters, 2001, 79, 1432-1434.	3.3	55
101	RBS ANALYSIS OF MBE GROWN SiGe/(001)Si HETEROSTRUCTURES WITH THIN HIGH Ge CONTENT SiGe CHANNELS FOR HMOS TRANSISTORS. Modern Physics Letters B, 2001, 15, 1297-1304.	1.9	5
102	X-ray absorption analysis of KDP optics. Journal of Electron Spectroscopy and Related Phenomena, 2001, 114-116, 873-878.	1.7	22
103	Depth Resolved Studies of Indium Content and Strain in InGaN Layers. Physica Status Solidi (B): Basic Research, 2001, 228, 59-64.	1.5	7
104	Amorphization of GaN by ion implantation. Nuclear Instruments & Methods in Physics Research B, 2001, 178, 200-203.	1.4	15
105	Coherent amorphization of Ge/Si multilayers with ion beams. Nuclear Instruments & Methods in Physics Research B, 2001, 178, 279-282.	1.4	2
106	Fe ion implantation in GaN: Damage, annealing, and lattice site location. Journal of Applied Physics, 2001, 90, 81-86.	2.5	24
107	Compositional dependence of the strain-free optical band gap in In _x Ga _{1-x} N layers. Applied Physics Letters, 2001, 78, 2137-2139.	3.3	104
108	Strain and Compositional Analysis of InGaN/GaN Layers. Materials Research Society Symposia Proceedings, 2000, 639, 3521.	0.1	3

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109	Wettability and Nanotribological Response of Silicon Surfaces Functionalized by Ion Implantation. Materials Science Forum, 0, 730-732, 257-262.	0.3	1